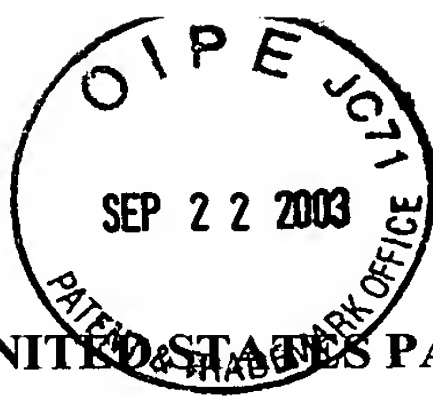


2812



Docket No. 239525US2/shb

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: 10/603,771

GAU: 2812

FILED: June 26, 2003

EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, OPTICAL MEMBER FOR USE IN CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, THIN FILM TRANSISTOR, AND DISPLAY

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Marvin J. Spivak

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Joseph A. Scafetta, Jr.

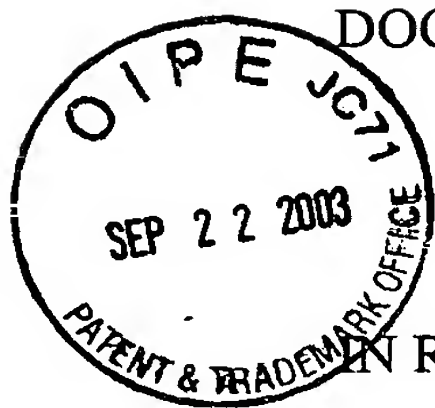
Registration No. 26,803

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DOCKET NO.: 239525US2/shb



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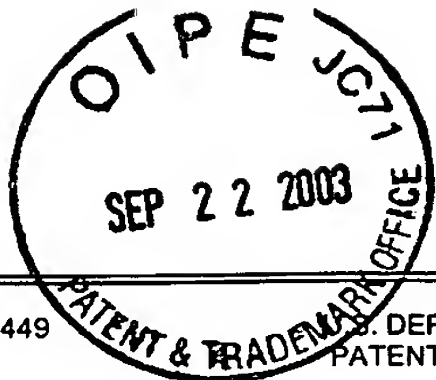
EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, OPTICAL MEMBER FOR USE IN
CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, THIN
FILM TRANSISTOR, AND DISPLAY

STATEMENT OF RELEVANCY

Reference AZ on Form 1449:

Fig. 4 illustrates a phenomenon wherein a laser beam undergoes phase modulation at the shifting portion of a phase shift mask, thereby inclining the wavefront.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

239525US2

SERIAL NO.

10/603,771

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yukio TANIGUCHI, et al.

FILING DATE

June 26, 2003

GROUP

2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AV	W. YEH, et al., Jpn. J. Appl. Phys., vol. 41, part 1, no. 4A, pages 1909-1914, "PROPOSED SAMPLE STRUCTURE FOR MARKED ENLARGEMENT OF EXCIMER-LASER-INDUCED LATERAL GRAIN GROWTH IN Si THIN FILMS", April 2002				
	AW	M. NAKATA, et al., Jpn. J. Appl. Phys., vol. 40, part 1, no. 5A, pages 3049-3054, "A NEW NUCLEATION-SIT-CONTROL EXCIMER-LASER-CRYSTALLIZATION METHOD", May 2001				
	AX	C.-H. OH, et al., Jpn. J. Appl. Phys., vol. 37, part 2, no. 5A, pages L492-L495, "A NOVEL PHASE-MODULATED EXCIMER-LASER CRYSTALLIZATION METHOD OF SILICON THIN FILMS", May 1998				
	AY	M. MATSUMURA, et al., Thin Solid Films 337, pages 123-128, "ADVANCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999				
	AZ	M. MATSUMURA, Applied Physics, vol. 71, no. 5, pages 543-547, "EXCIMER-LASER-GROWN SILICON THIN FILMS WITH ULTRALARGE GRAINS", 2002				<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.